

# Vishay General Semiconductor

# Trench MOS Barrier Schottky Rectifier for PV Solar Cell Bypass Protection

Ultra Low  $V_F = 0.33 \text{ V}$  at  $I_F = 5.0 \text{ A}$ 



## **DESIGN SUPPORT TOOLS**

click logo to get started



| PRIMARY CHARACTERISTICS                  |                               |  |  |  |
|--|-------------------------------|--|--|--|
| I <sub>F(AV)</sub>                       | 2 x 10 A                      |  |  |  |
| $V_{RRM}$                                | 45 V                          |  |  |  |
| I <sub>FSM</sub>                         | 160 A                         |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> = 10 A  | 0.41 V                        |  |  |  |
| T <sub>OP</sub> max. (AC mode)           | 150 °C                        |  |  |  |
| T <sub>J</sub> max. (DC forward current) | 200 °C                        |  |  |  |
| Package                                  | D <sup>2</sup> PAK (TO-263AB) |  |  |  |
| Circuit configuration                    | Common cathode                |  |  |  |

#### **FEATURES**

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- · High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



- T<sub>J</sub> 200 °C max. in solar bypass mode application
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

For use in solar cell junction box as a bypass diode for protection, using DC forward current without reverse bias.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK (TO-263AB)

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs maximum

| MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)                              |            |                                    |             |      |  |
|--|------------|------------------------------------|-------------|------|--|
| PARAMETER  |            | SYMBOL                             | VBT2045CBP  | UNIT |  |
| Maximum repetitive peak reverse voltage  |            | $V_{RRM}$                          | 45          | V    |  |
| Maximum average forward rectified current (fig. 1)   | per device | I <sub>F(AV)</sub> <sup>(1)</sup>  | 20          | А    |  |
|  | per diode  |                                    | 10          |      |  |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode |            | I <sub>FSM</sub>                   | 160         | А    |  |
| Operating junction and storage temperature range (AC mode)                                   |            | T <sub>OP</sub> , T <sub>STG</sub> | -40 to +150 | °C   |  |
| Junction temperature in DC forward current without reverse bias, t $\leq$ 1 h                |            | T <sub>J</sub> <sup>(2)</sup>      | ≤ 200       | °C   |  |

#### Notes

- (1) With heatsink
- (2) Meets the requirements of IEC 61215 ed. 2 bypass diode thermal test



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| <b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted) |                            |   |                               |      |      |      |
|---|----------------------------|---|-------------------------------|------|------|------|
| PARAMETER   | TEST CONDITIONS            |   | SYMBOL                        | TYP. | MAX. | UNIT |
| Instantaneous forward voltage per diode   | I <sub>F</sub> = 5 A       | T <sub>A</sub> = 25 °C                            | V <sub>F</sub> <sup>(1)</sup> | 0.44 | -    | V    |
|   | I <sub>F</sub> = 10 A      |   |                               | 0.49 | 0.58 |      |
|   | I <sub>F</sub> = 5 A       | T <sub>A</sub> = 125 °C                           |                               | 0.33 | -    |      |
|   | I <sub>F</sub> = 10 A      |   |                               | 0.41 | 0.52 |      |
| Reverse current per diode   | $V_R = 45 \text{ V}$ $T_A$ | T <sub>A</sub> = 25 °C<br>T <sub>A</sub> = 125 °C | I <sub>R</sub> <sup>(2)</sup> | -    | 2000 | μA   |
|   |                            | T <sub>A</sub> = 125 °C                           |                               | 10   | 30   | mA   |

#### Notes

<sup>(2)</sup> Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |            |               |            |      |  |
|---|------------|---------------|------------|------|--|
| PARAMETER   |            | SYMBOL        | VBT2045CBP | UNIT |  |
| Typical thermal resistance  | per diode  | $R_{	hetaJC}$ | 3.0        | °C/W |  |
|   | per device |               | 2.0        |      |  |

| ORDERING INFORMATION (Example) |                  |                 |              |               |               |  |
|--------------------------------|------------------|-----------------|--------------|---------------|---------------|--|
| PACKAGE                        | PREFERRED P/N    | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |  |
| TO-263AB                       | VBT2045CBP-E3/4W | 1.38            | 4W           | 50/tube       | Tube          |  |
| TO-263AB                       | VBT2045CBP-E3/8W | 1.38            | 8W           | 800/reel      | Tape and reel |  |

## RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)

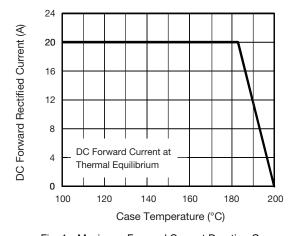


Fig. 1 - Maximum Forward Current Derating Curve

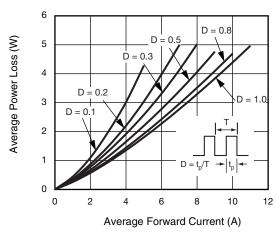


Fig. 2 - Forward Power Loss Characteristics Per Diode

<sup>(1)</sup> Pulse test: 300 µs pulse width, 1 % duty cycle



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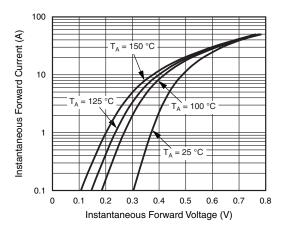


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

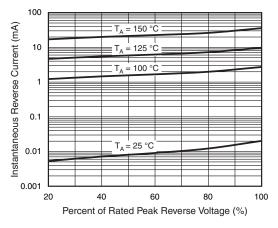


Fig. 4 - Typical Reverse Characteristics Per Diode

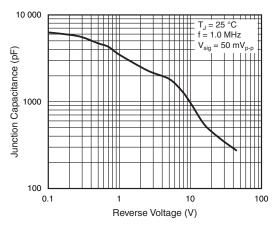


Fig. 5 - Typical Junction Capacitance Per Diode

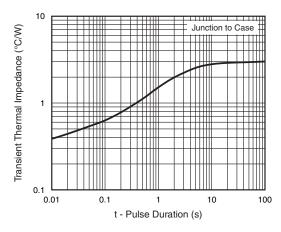
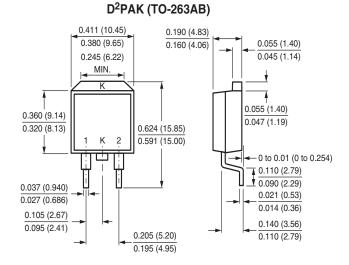
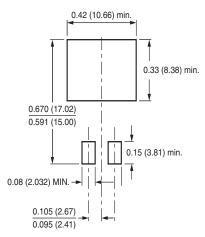


Fig. 6 - Typical Transient Thermal Impedance Per Diode

## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



## **Mounting Pad Layout**





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